

**DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

**Product Summary**

Device	BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
N-Channel	12V	150mΩ @ V <sub>GS</sub> = 4.5V	2.0A
		185mΩ @ V <sub>GS</sub> = 2.5V	1.8A

**Features and Benefits**

- Footprint of just 1.3 mm<sup>2</sup>
- Ultra-Low Profile Package – 0.35mm Profile
- Low Gate Threshold Voltage
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

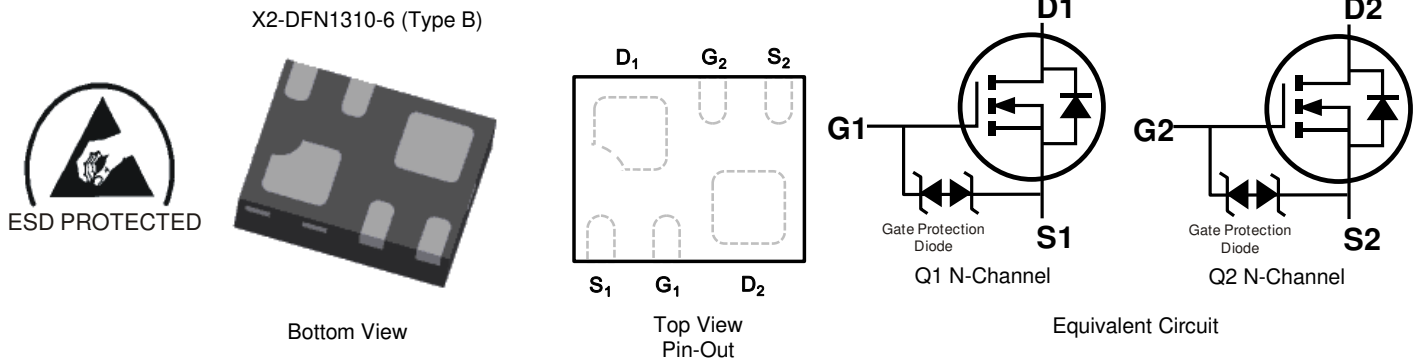
**Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Power Management Functions
- Backlighting

**Mechanical Data**

- Case: X2-DFN1310-6 (Type B)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.002 grams (Approximate)



**Ordering Information (Note 4)**

Part Number	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMN1150UFL3-7	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



150 = Product Type Marking Code

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	12	V
Gate-Source Voltage			$V_{GSS}$	$\pm 6$	V
Continuous Drain Current (Note 5) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	2.0	A
		$T_A = +70^\circ\text{C}$		1.6	

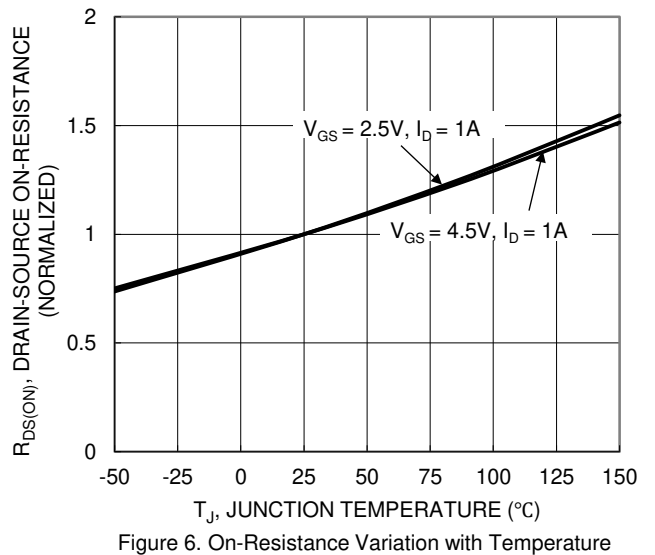
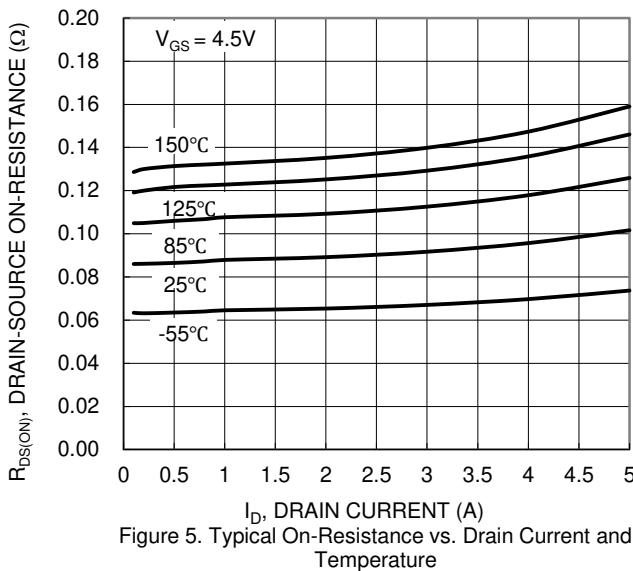
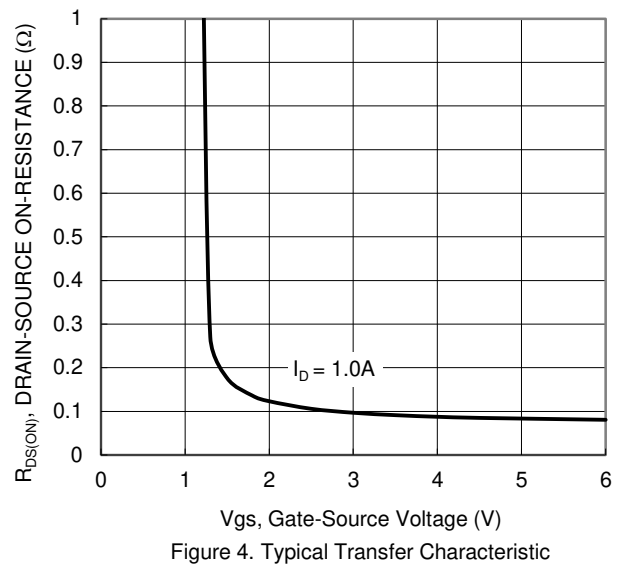
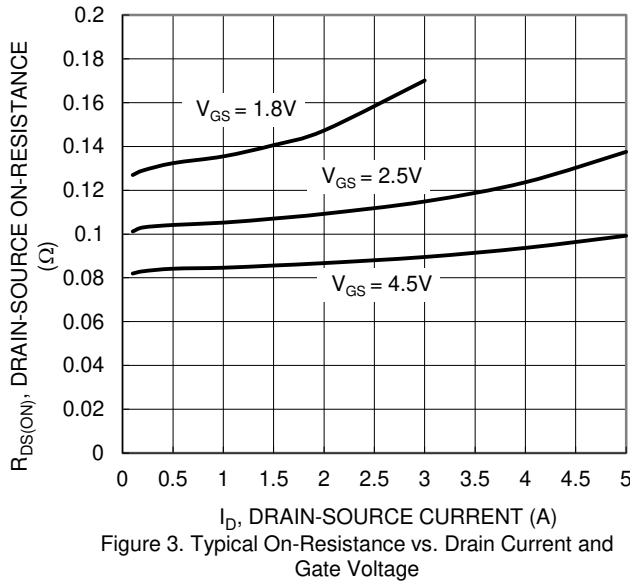
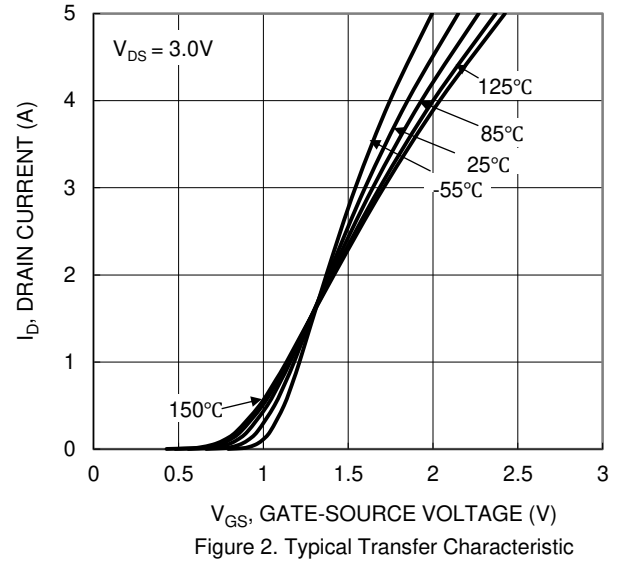
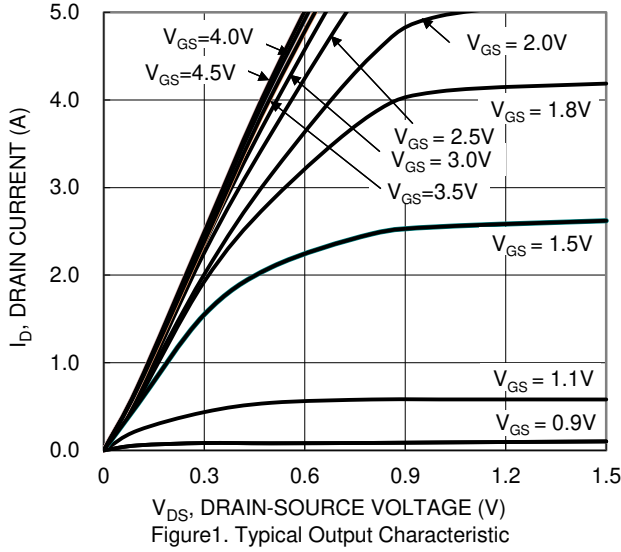
**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

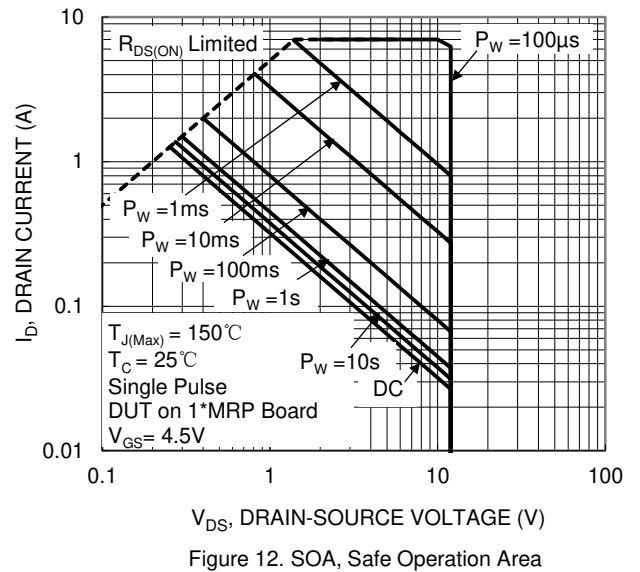
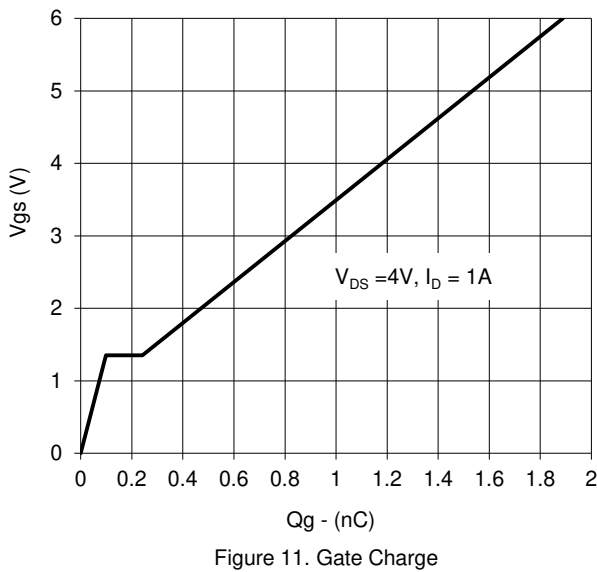
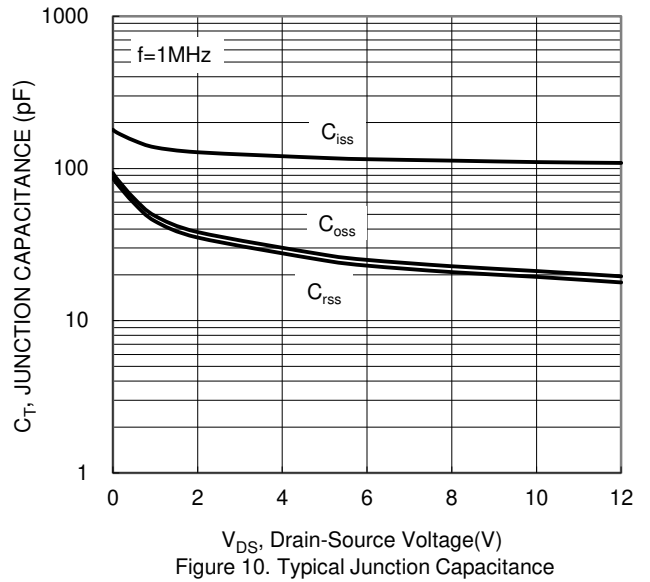
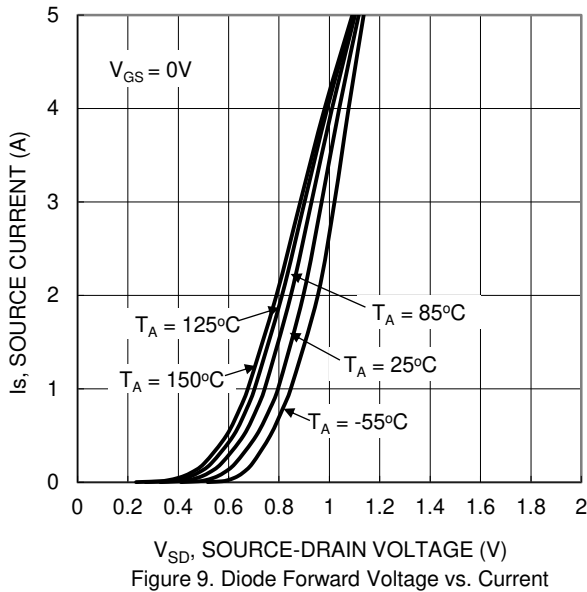
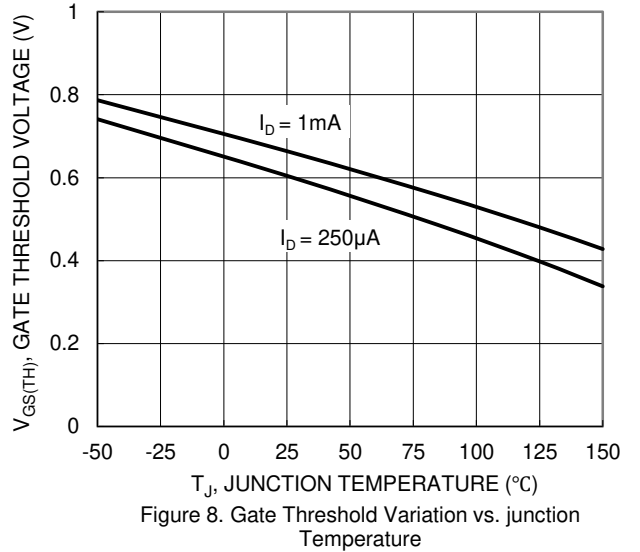
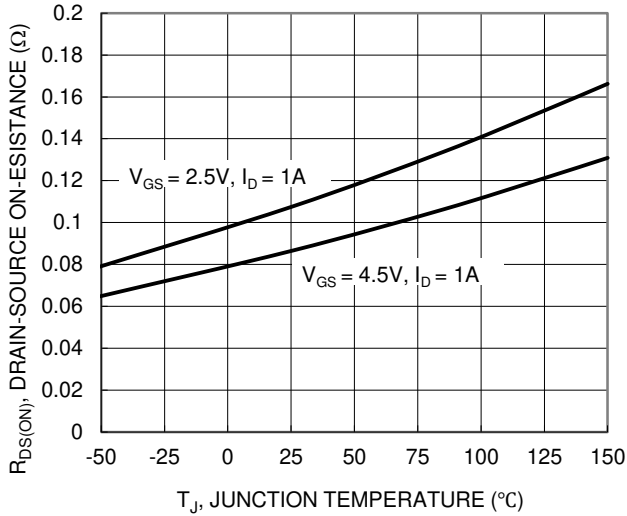
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	$P_D$	0.39	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	320	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$	$P_D$	0.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	141	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	49	
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	$BV_{DSS}$	12	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 12\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 6\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.35	0.42	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	119	150	m $\Omega$	$V_{GS} = 4.5\text{V}, I_D = 1\text{A}$
			141	185		$V_{GS} = 2.5\text{V}, I_D = 1\text{A}$
			175	210		$V_{GS} = 1.8\text{V}, I_D = 1\text{A}$
Diode Forward Voltage	$V_{SD}$	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 150\text{mA}$
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	$C_{ISS}$	—	115	—	pF	$V_{DS} = 6\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	$C_{OSS}$	—	25	—	pF	
Reverse Transfer Capacitance	$C_{RSS}$	—	23	—	pF	
Gate Resistance	$R_G$	—	90	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge	$Q_G$	—	1.4	—	nC	$V_{DS} = 4\text{V}, V_{GS} = 4.5\text{V}, I_D = 1\text{A}$
Gate-Source Charge	$Q_{GS}$	—	0.1	—	nC	
Gate-Drain Charge	$Q_{GD}$	—	0.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.0	—	ns	$V_{GS} = 6\text{V}, V_{DS} = 4\text{V}, R_G = 1\Omega, I_D = 1\text{A}$
Turn-On Rise Time	$t_R$	—	7.4	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	44	—	ns	
Turn-Off Fall Time	$t_F$	—	19	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1 inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.





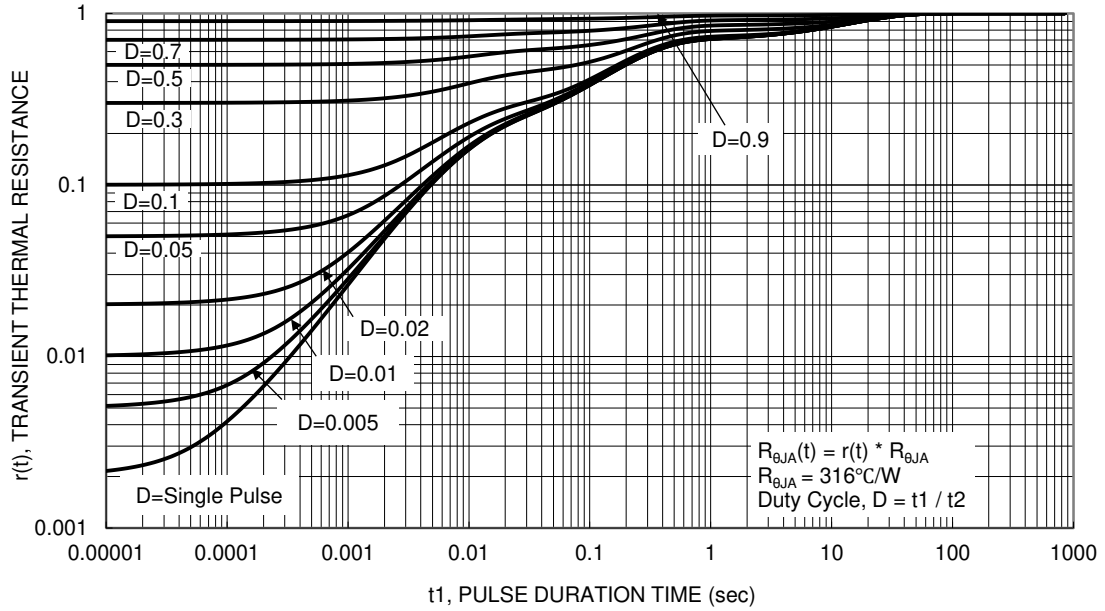
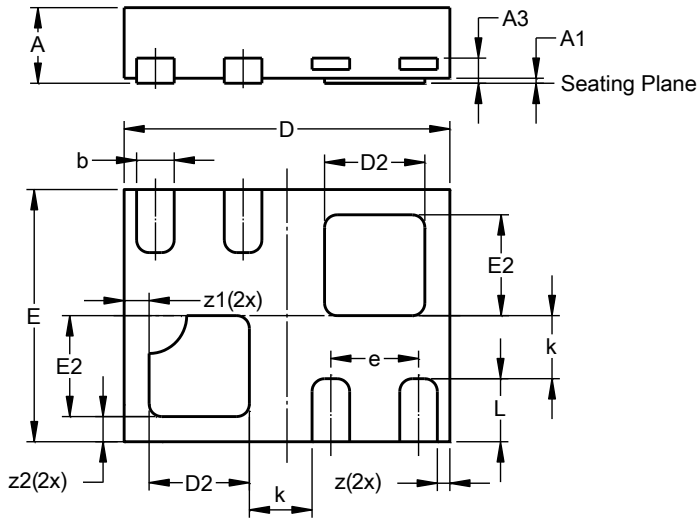


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**X2-DFN1310-6 (Type B)**

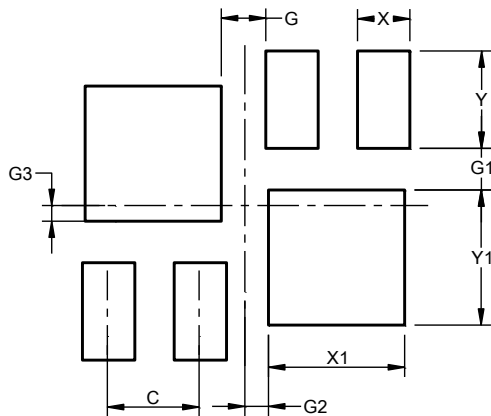


X2-DFN1310-6 (Type B)			
Dim	Min	Max	Typ
A	0.25	0.35	0.30
A1	0	0.05	0.02
A3	--	--	0.100
b	0.10	0.20	0.15
D	1.25	1.35	1.30
D2	0.30	0.50	0.40
E	0.95	1.05	1.00
E2	0.30	0.50	0.40
e	--	--	0.35
k	0.15	--	--
L	0.20	0.30	0.25
z	--	--	0.05
z1	--	--	0.10
z2	--	--	0.10
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**X2-DFN1310-6 (Type B)**



Dimensions	Value (in mm)
C	0.350
G	0.17
G1	0.16
G2	0.09
G3	0.06
X	0.20
X1	0.52
Y	0.375
Y1	0.52

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